



20V Complementary Enhancement Mode MOSFET

Voltage

20 / -20V

Current

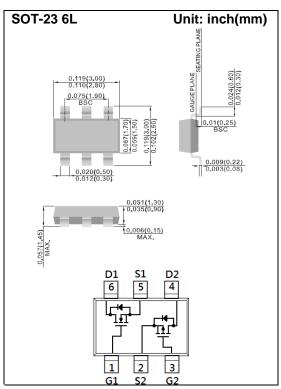
5.2 /-3.4A

Features

- Advanced Trench Process Technology
- Specially Designed for Switch Load, PWM Application, etc.
- Lead free in compliance with EU RoHS 2011/65/EU directive
- Green molding compound as per IEC61249 Std. (Halogen Free)

Mechanical Data

- Case: SOT-23 6L Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.0005 ounces, 0.014 grams
- Marking: SC2



Maximum Ratings and Thermal Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	N-Ch LIMIT	P-Ch LIMIT	UNITS	
Drain-Source Voltage		V_{DS}	20	-20	V
Gate-Source Voltage		V_{GS}	<u>+</u> 12	<u>+</u> 12	V
Continuous Drain Current		I _D	5.2	-3.4	Α
Pulsed Drain Current (Note 4)		I _{DM}	20.8	-13.6	Α
B	T _a =25°C		1.25		W
Power Dissipation	Derate above 25°C	P_{D}	1	mW/°C	
Operating Junction and Storage Tem	T_J, T_{STG}	-55~150		°C	
Typical Thermal Resistance - Junction to Ambient (Note 3)		$R_{\theta JA}$	100		°C/W





N-Channel Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	20	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250uA$	0.5	0.77	1.2	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =4.5V, I _D =5.2A	-	29	36	mΩ
		V _{GS} =2.5V, I _D =3.2A	-	39	52	
		V _{GS} =1.8V, I _D =1.5A	-	58	92	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =20V, V _{GS} =0V	-	-	1	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} = <u>+</u> 12V, V _{DS} =0V	-	-	<u>+</u> 100	nA
Dynamic (Note 5)						
Total Gate Charge	Q_g	101/ 1 5 0 0	-	4.1	-	nC
Gate-Source Charge	Q_gs	V _{DS} =10V, I _D =5.2A, V _{GS} =4.5V ^(Note 1,2)	-	1.1	-	
Gate-Drain Charge	Q_gd	V _{GS} =4.5V	-	0.7	-	
Input Capacitance	Ciss	V _{DS} =10V, V _{GS} =0V, f=1.0MHZ	-	396	-	pF
Output Capacitance	Coss		-	54	-	
Reverse Transfer Capacitance	Crss		-	40	-	
Turn-On Delay Time	td _(on)	\/ 40\/ L 50A	-	14	-	ns
Turn-On Rise Time	tr	V_{DD} =10V, I_{D} =5.2A, V_{GS} =4.5V, R_{G} =6 Ω (Note 1,2)	-	10	-	
Turn-Off Delay Time	td _(off)		-	30	-	
Turn-Off Fall Time	tf		-	7	-	
Drain-Source Diode						
Maximum Continuous Drain-Source					1.5	Α
Diode Forward Current	I _S		-	-	1.0	^
Diode Forward Voltage	V_{SD}	I _S =1.0A, V _{GS} =0V	-	0.75	1.2	V

NOTES:

- 1. Pulse width<a>300us, Duty cycle<a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. ROJA is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
- 4. The maximum current rating is package limited.
- 5. Guaranteed by design, not subject to production testing





P-Channel Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250uA	-20	-	-	V	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=-250uA$	-0.4	-0.65	-1.2	V	
Drain-Source On-State Resistance		V_{GS} =-4.5V, I_{D} =-3.4A	-	65	82	mΩ	
	R _{DS(on)}	V_{GS} =-2.5V, I_{D} =-2.2A	-	82	110		
		V _{GS} =-1.8V, I _D =-1.2A	-	103	146		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-20V, V _{GS} =0V	-	-	-1	uA	
Gate-Source Leakage Current	I _{GSS}	V _{GS} = <u>+</u> 12V, V _{DS} =0V	-	-	<u>+</u> 100	nA	
Dynamic (Note 5)							
Total Gate Charge	Q_{g}	\/ 40\/ L 2.4A	-	7	-	nC	
Gate-Source Charge	Q_gs	V_{DS} =-10V, I_{D} =-3.4A, V_{GS} =-4.5V (Note 1,2)	-	1	-		
Gate-Drain Charge	Q_{gd}	V _{GS} =-4.5 V	-	1.8	-		
Input Capacitance	Ciss	V _{DS} =-10V, V _{GS} =0V, f=1.0MHZ	-	522	-	pF	
Output Capacitance	Coss		-	55	-		
Reverse Transfer Capacitance	Crss		-	40	-		
Turn-On Delay Time	td _(on)	\/ 40\/ L 2.44	-	10	-	ns	
Turn-On Rise Time	tr	V_{DD} =-10V, I_{D} =-3.4A, V_{GS} =-4.5V, R_{G} =6 Ω (Note 1,2)	-	4	-		
Turn-Off Delay Time	td _(off)		-	34	-		
Turn-Off Fall Time	tf		-	5	-		
Drain-Source Diode							
Maximum Continuous Drain-Source					1 5	Α	
Diode Forward Current	I _S		_	-	-1.5	^	
Diode Forward Voltage	V_{SD}	I _S =-1.0A, V _{GS} =0V	-	0.77	-1.2	V	

NOTES:

- 1. Pulse width<a>300us, Duty cycle<a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. ROJA is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
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N-Channel TYPICAL CHARACTERISTIC CURVES

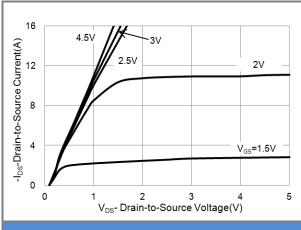


Fig.1 On-Region Characteristics

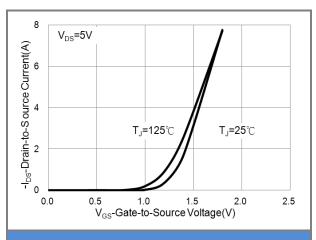


Fig.2 Transfer Characteristics

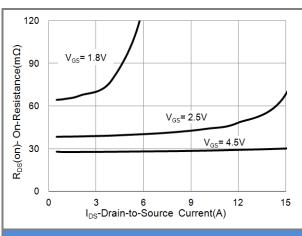


Fig.3 On-Resistance vs. Drain Current

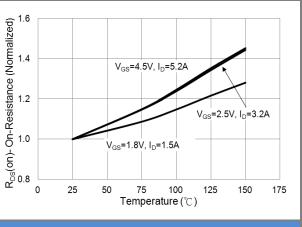
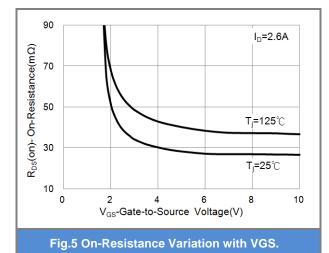
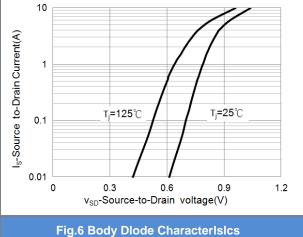


Fig.4 On-Resistance vs. Junction temperature









N-Channel TYPICAL CHARACTERISTIC CURVES

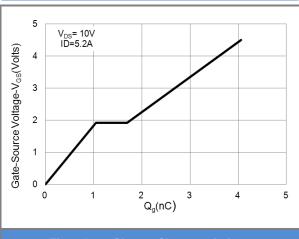


Fig.7 Gate-Charge Characteristics

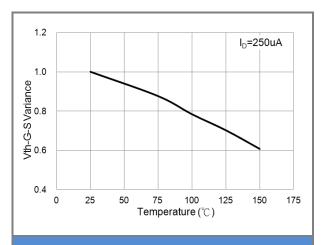


Fig.8 Threshold Voltage Variation with Temperature.

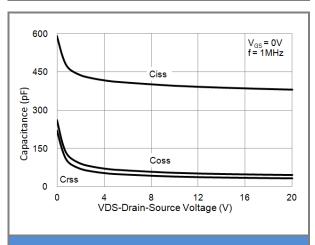


Fig.9 Capacitance vs. Drain-Source Voltage.





P-Channel TYPICAL CHARACTERISTIC CURVES

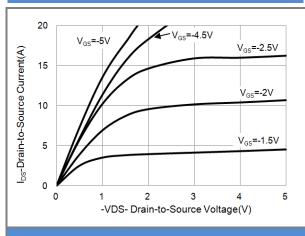


Fig.1 On-Region Characteristics

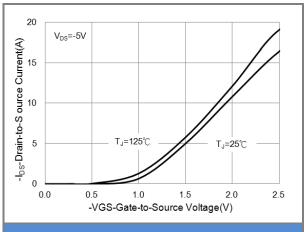


Fig.2 Transfer Characteristics

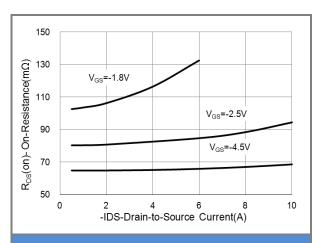


Fig.3 On-Resistance vs. Drain Current

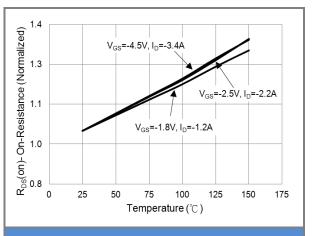
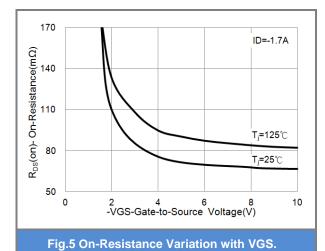


Fig.4 On-Resistance vs. Junction temperature









P-Channel TYPICAL CHARACTERISTIC CURVES

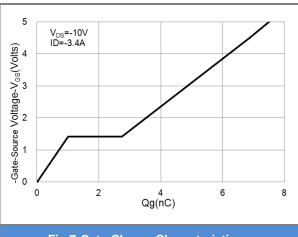


Fig.7 Gate-Charge Characteristics

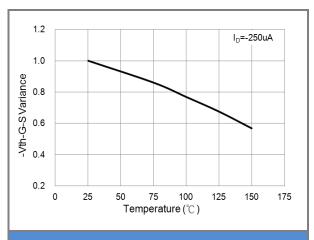


Fig.8 Threshold Voltage Variation with Temperature.

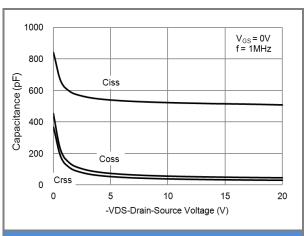


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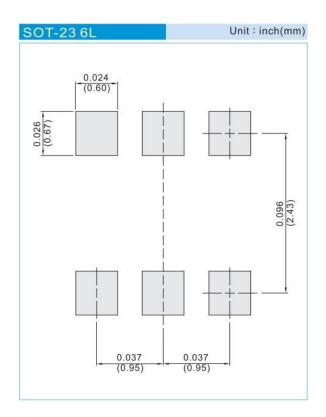




PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing type	Marking	Version
PJS6602_S1_00001	SOT-23 6L	3K pcs / 7" reel	SC2	Halogen free
PJS6602_S2_00001	SOT-23 6L	10K pcs / 13" reel	SC2	Halogen free

MOUNTING PAD LAYOUT







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